

Silicon PNP Power Transistors

2SB691

DESCRIPTION

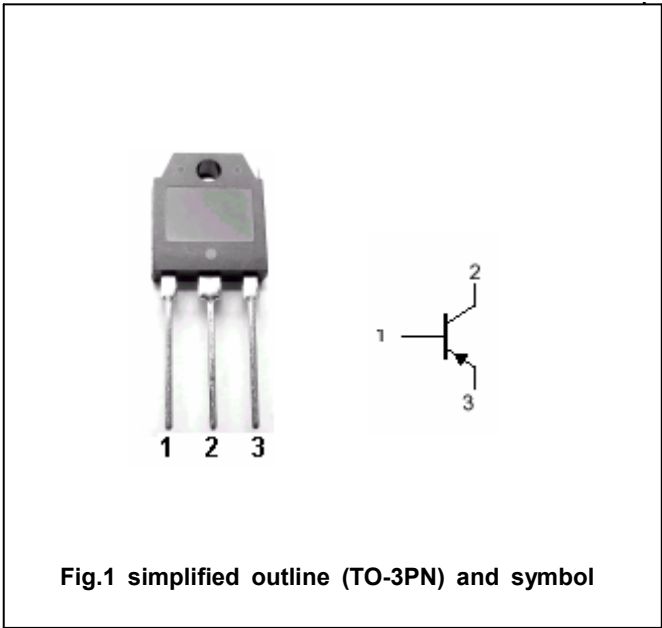
- With TO-3PN package
- Wide area of safe operation

APPLICATIONS

- For low frequency power amplifier and power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Tc=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-130	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
P_C	Collector power dissipation	$T_C=25^{\circ}C$	60	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -30mA ; I_B = 0$	-80			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -1mA ; I_E = 0$	-130			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -1mA ; I_C = 0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -3A ; I_B = -0.3A$			-1.5	V
V_{BE}	Base-emitter on voltage	$I_C = -1A ; V_{CE} = -5V$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB} = -130V ; I_E = 0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5V ; I_C = 0$			-0.1	mA
h_{FE-1}	DC current gain	$I_C = -1A ; V_{CE} = -5V$	40		200	
h_{FE-2}	DC current gain	$I_C = -3A ; V_{CE} = -5V$	20			
f_T	Transition frequency	$I_C = -1A ; V_{CE} = -5V$		7		MHz

PACKAGE OUTLINE

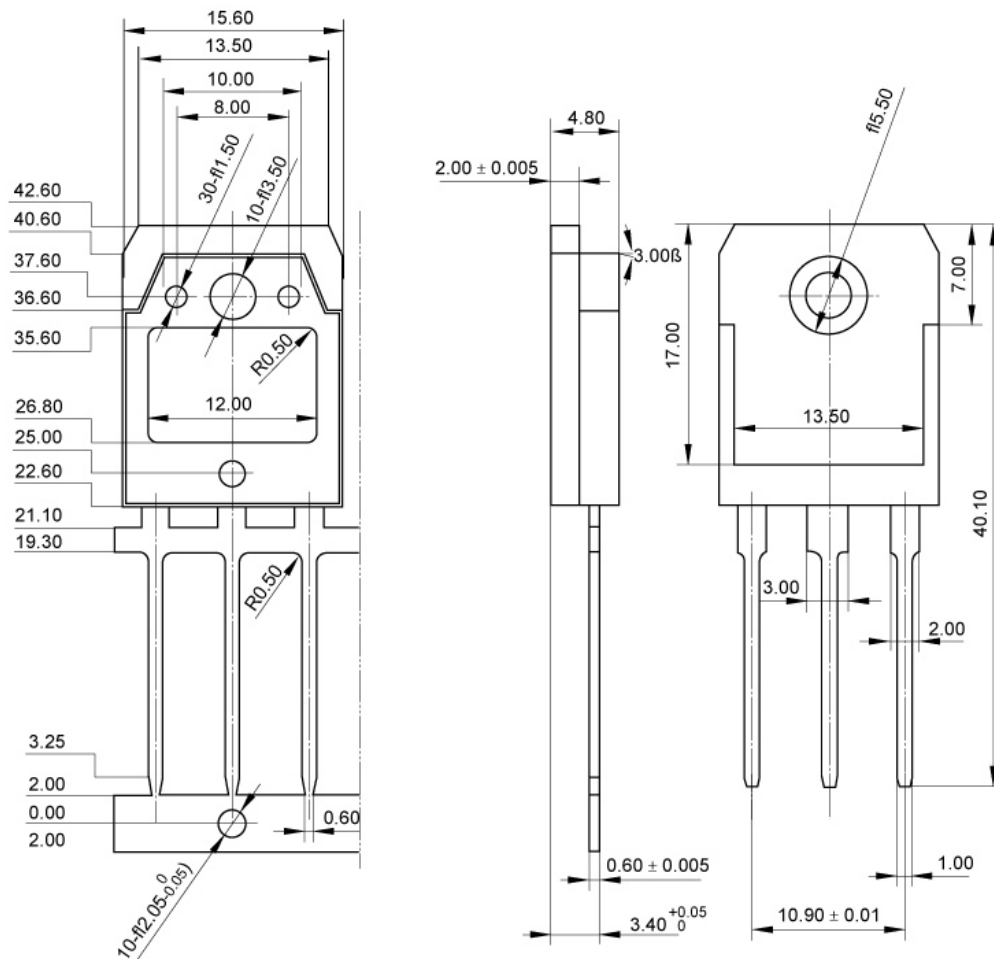


Fig.2 outline dimensions